EMB3 / UMB3N / IMB3A

PNP -100mA -50V Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Tr1 and Tr2
$V_{\sf CEO}$	-50V
I _{C(MAX.)}	-100mA
R ₁	4.7 k Ω

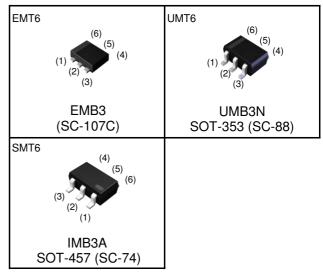
Features

- 1) Built-In Biasing Resistors.
- 2) Two DTA143T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

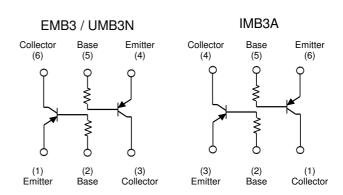
Application

Inverter circuit, Interface circuit, Driver circuit

Outline



●Inner circuit



Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMB3	EMT6	1616	T2R	180	8	8,000	В3
UMB3N	UMT6	2021	TR	180	8	3,000	В3
IMB3A	SMT6	2928	T108	180	8	3,000	В3

● Absolute maximum ratings (Ta = 25 °C)

<For Tr1 and Tr2 in common>

Paramete	Symbol	Values	Unit	
Collector-base voltage		V_{CBO}	-50	V
Collector-emitter voltage		V_{CEO}	-50	V
Emitter-base voltage		V _{EBO}	– 5	V
Collector current		I _{C(MAX.)} *1	-100	mA
Collector Power dissipation	EMB3 / UMB3N	P _D *2	150 (Total)*3	mW
IMB3A			300 (Total)*4	mW
Junction temperature		T _j	150	∞
Range of storage temperature		T _{stg}	−55 to +150	∞

●Electrical characteristics(Ta = 25 °C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV_CBO	$I_C = -50 \mu A$	-50	-	-	V
Collector-emitter breakdown voltage	BV_CEO	$I_C = -1 \text{mA}$	-50	-	1	V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50 \mu A$	-5	-	1	V
Collector cut-off current	I _{CBO}	$V_{CB} = -50V$	1	-	-0.5	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -4V$	ı	1	-0.5	μΑ
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C}$ / $I_{\rm B}$ = -5mA / -0.25mA	ı	ı	-0.3	V
DC current gain	h _{FE}	$V_{CE} = -5V$, $I_C = -1mA$,	100	250	600	-
Input resistance	R ₁	-	3.29	4.7	6.11	kΩ
Transition frequency	f _T *1	$V_{CE} = -10V, I_{E} = 5mA,$ f = 100MHz	-	250	-	MHz

^{*1} Characteristics of built-in transistor

^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

^{*4 200}mW per element must not be exceeded.

●Electrical characteristic curves(Ta = 25 °C)

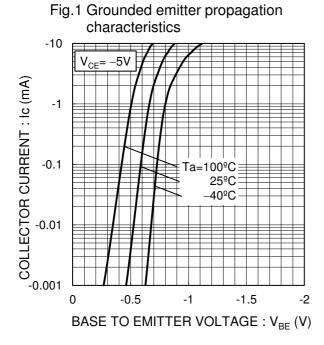
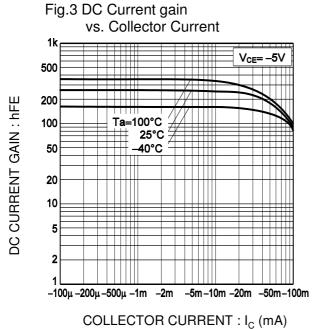


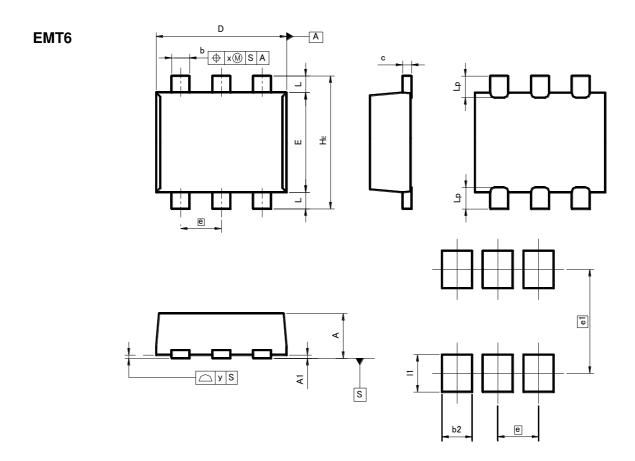
Fig.2 Grounded emitter output characteristics -100 $I_B =$ Ta=25ºC 500µA 450µA COLLECTOR CURRENT : I_C (mA) -80 -400µA -350µA 300µA -60 -250µA -200µA -40 -150µA -100µA -20 -50µA 0 0 -2 -6 -8 -10 **COLLECTOR TO EMITTER** VOLTAGE: V_{CF} (V)

Fig.4 Collector-emitter saturation voltage



vs. Collector Current $I_C/I_B=20$ -500m Ta=100°C 25°C **SOLLECTOR SATURATION** -200m VOLTAGE: V_{CE}(sat) (V) -100m -50m -20m -10m -5m -2m -1m $-100 \mu \ -200 \mu \ -500 \mu \ -1m \quad -2m \quad -5m \ -10m \ -20m \ \ -50m -100m$ COLLECTOR CURRENT : I_C (mA)

● **Dimensions** (Unit: mm)



Patterm of terminal position areas

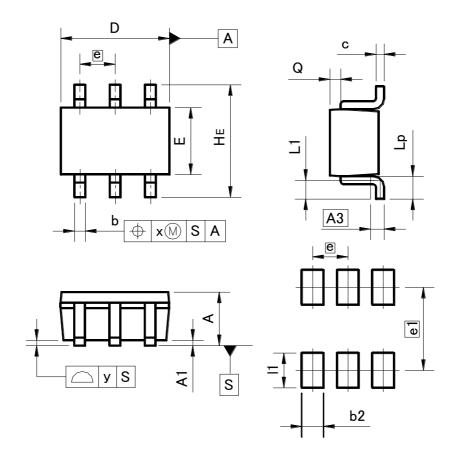
DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.10	0	0.004
Α	0.45	0.55	0.018	0.022
b	0.17	0.27	0.007	0.011
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
е	0.	50	0.02	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	_	0.35	_	0.014
х	_	0.10		0.004
У	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
MIN		MAX	MIN	MAX	
e1	1.25		0.049		
b2	-	- 0.37		0.015	
l1	_	0.45	_	0.018	

Dimension in mm/inches

● **Dimensions** (Unit: mm)

UMT6



Patterm of terminal position areas

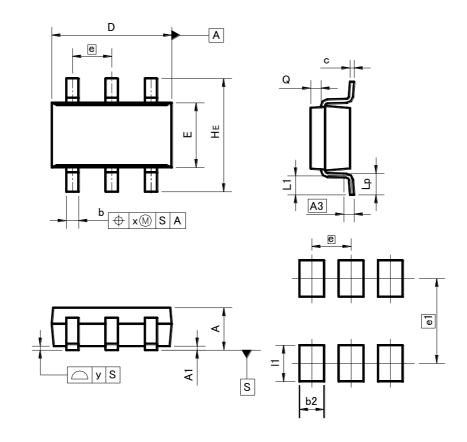
DIM MILI		ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.80	1.00	ı	0.039
A1	0.00	0.10	0	0.004
A3	0.2	25	0.0	01
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.0	65	0.03	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.02
Lp	0.25	0.55	0.01	0.022
Q	0.10	0.30	0.004	0.012
х	_	0.10	-	0.004
у	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
e1	1.55		0.06		
b2	-	0.40	_	0.016	
11	1	0.65	ı	0.026	

Dimension in mm/inches

● **Dimensions** (Unit: mm)

SMT6



Patterm of terminal position areas

DIM	MILIMI	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	1.00	1.30	0.039	0.051
A1	0.00	0.10	0	0.004
A3	0.2	25	0.0	01
b	0.25	0.40	0.01	0.016
С	0.09	0.25	0.004	0.01
D	2.80	3.00	0.11	0.118
E	1.50	1.80	0.059	0.071
е	0.9	95	0.04	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20	_	0.008
у	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2	0.60		_	0.024	
11	_	0.90	-	0.035	

Dimension in mm/inches

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